Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 75, 77, 78, 79, 85, 86, 95-99, and amend claims 73, 76, 81, 84, and 91 as follows:

Listing of Claims:

1-72. (Cancelled)

73. (Currently Amended) An in-process device, comprising:

a substrate; ~~and~~

a conductive layer over said substrate and having a surface stuffed with a non-oxygen material; and

a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer, wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

74. (Original) The in-process device of claim 73, wherein said surface is a nitrogen-stuffed surface.

75. (Cancelled)

76. (Currently Amended) The in-process device of claim 73 wherein the conductive layer has been exposed to a material ~~carbon-silicon compound is~~ selected from the group consisting of methylsilane, hexamethyldisilane and hexamethyldisilazane.

77.-79. (Cancelled)

80. (Previously Presented) The in-process device of claim 73 wherein the substrate comprises a silicon substrate.

81. (Currently Amended) An in-process device, comprising:

a substrate; ~~and~~

a passivated conductive layer over the substrate, the passivated conductive layer having a reduced ability to associate with oxygen by being exposed to a material selected from the group consisting of phosphine and methylsilane; and

a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer, wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

82. (Previously Presented) The in-process device of claim 81 wherein the conductive layer comprises tungsten nitride.

83. (Previously Presented) The in-process device of claim 82 further comprising another conductive layer formed on the tungsten nitride layer.

84. (Currently Amended) The in-process device of claim 83 wherein the ~~other~~ another conductive layer comprises copper.

85.-86 (Cancelled)

87. (Previously Presented) The in-process device of claim 81 wherein the substrate comprises a silicon substrate.

88. (Previously Presented) An in-process device, comprising:

a substrate; and

a passivated conductive layer over the substrate, the passivated conductive layer having a reduced ability to associate with oxygen by being exposed to methylsilane.

89. (Previously Presented) The in-process device of claim 88 wherein the conductive layer comprises tungsten nitride.

90. (Previously Presented) The in-process device of claim 89 further comprising another conductive layer formed on the tungsten nitride layer.

91. (Currently Amended) The in-process device of claim 90 wherein the ~~other~~ another conductive layer comprises copper.

92. (Previously Presented) The in-process device of claim 88 further comprising a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer.

93. (Previously Presented) The in-process device of claim 92 wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

94. (Previously Presented) The in-process device of claim 88 wherein the substrate comprises a silicon substrate.

95.-99. (Cancelled)